

# Citations for Ion : **P**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
<b>1949</b>	Boggild, J. K. Minnhagen, L. 'A Cloud-Chamber Study of the Disintegration of Lithium by Slow Neutrons' <i>Phys. Rev.</i> , 75, 782-85 (1949) <i>Comment</i> : R. 880-keV H -> Air	1949-Bogg
<b>1957</b>	Bichsel, H. Mozley, R. F. Aron, W. A. 'Range of 6- to 18-MeV Protons in Be, Al, Cu, Ag and Au' <i>Phys. Rev.</i> , 105, 1788-95 (1957) <i>Comment</i> : R. 6-18 MeV H -> Be, Al, Cu, Ag, Au	1957-Bich
<b>1962</b>	Teplova, Ya. A. Nikolaev, V. S. Dimitriev, I. S. Fateeva, L. N. 'Slowing Down of Multicharged Ions in Solids and Gases' <i>Zh. Eksp. Teor. Fiz.</i> , 42, 44-60 (1962)[ <i>Engl. Trans. Sov. Phys., JETP</i> 15, 31-41 (1962)] <i>Comment</i> : S, R. (75-1500 keV/amu) He, Li, Be, B, C, N, O, Ne, Na, Mg, Al, P, Cl, K, Br, Kr -> H <sub>2</sub> , He, CH <sub>4</sub> , Benzene, Air, Ar, S. Same -> Al, Ni, Ag, Au	1962-Tepl
<b>1965</b>	Davies, J. A. Erikson, L. Jespersgaard, P. 'The Range of Heavy Ions (0.1 - 1.5 MeV) in Monocrystalline Tungsten.' <i>Nucl. Inst. Methods</i> , 38, 245-48 (1965) <i>Comment</i> : R, dR. 0.1 - 1.5 MeV Na, P, K, Kr, Xe -> W (Cryst.)	1965-Davi
<b>1966</b>	Fastrup, B. Hvelplund, P. Sautter, C. A. 'Stopping Cross Section in Carbon of 0.1-1.0 MeV Atoms with 5<Z<20' <i>Kgl. Danske Videnskab. Selskab. Mat. Fys. Medd.</i> , 35, No. 10, 1-28 (1966) <i>Comment</i> : S. (80-900 keV) H, C, N, O, F, Ne, Na, Mg, Al, Si, P, S, Cl, Ar->C	1966-Fast
<b>1966</b>	Palmer, R. B. J. 'The Stopping of Hydrogen and Hydrocarbon Vapours for Alpha Particles over the Energy Range 1-8 MeV' <i>Proc. Phys. Soc.</i> , 87, 681-88 (1966) <i>Comment</i> : S. 1-8 MeV He -> H, C, Many Hydrocarbons	1966-Palm
<b>1967</b>	Erikson, L. Davies, J. A. Jespersgaard, P. 'Range Measurements in Oriented Tungsten Single Crystals (0.1-1.0 MeV). Part I: Electronic and Nuclear Stopping Powers.' <i>Phys. Rev.</i> , 161, 219-34 (1967) <i>Comment</i> : R, dR. (0.1-1.0 MeV) Na, P, K, Cr, Cu, Br, Kr, Rb, Sb, Xe, W, Rn -> W (Cryst.); (40-500 keV) Na, K, Kr, Xe -> Al (Cryst.)	1967-Erik2
<b>1968</b>	Andersen, T. Sorensen, G. 'Range Studies using a New Chemical Film Technique' <i>Can. J. Phys.</i> , 46, 483-88 (1968) <i>Comment</i> : R, dR. 100-550 keV <sup>24</sup> Na, 150-500 keV <sup>32</sup> P, 100-500 keV <sup>42</sup> K -> Au	1968-Ande2
<b>1968</b>	Bowman, W. W. Lanzafame, F. M. Cline, C. K. Yu, Yu-Wen Blann, M. 'Recoil Ranges of 0.2 - 5.2 MeV Ions in Vanadium, Nickel, Iron, Zirconium and Gold.' <i>Phys. Rev.</i> , 165, 485-93 (1968) <i>Comment</i> : R, dR. Ion(ZI=12-81, E=0.22-5.2 MeV) -> V, Ni, Zr, Au	1968-Bowm

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<b>1968</b>	Dearnaley, G. Freeman, J. H. Gard, G. A. Williams, M. A. 'Implantation Profiles of 32P Channeled into Silicon Crystals' <i>Can. J. Phys.</i> , 46, 587-95 (1968) <i>Comment</i> : R, dR. 10-110 keV 32P -> Si (Cryst.)	1968-Dear
<b>1968</b>	Eisen, F. H. 'Channeling of Medium-Mass Ions through Silicon' <i>Can. J. Phys.</i> , 46, 561-72 (1968) <i>Comment</i> : S. 100-500 keV B, C, N, O, F, Ne, Na, Mg, Al, Si, P, Cl, Ar, K -> Si (Cryst.)	1968-Eise
<b>1968</b>	Fastrup, B. Borup, A. Hvelplund, P. 'Stopping Cross Section in Atmospheric Air of 0.2 - 0.5 MeV Atoms with $6 \leq Z1 \leq 24$ .' <i>Can. J. Phys.</i> , 46, 489-95 (1968) <i>Comment</i> : S. (100-1000 keV) C, N, O, Ne, N, Mg, P, S, Cl, Sc, Ca, Ti Al, Ar, K, Cr -> Air	1968-Fast
<b>1968</b>	Kleinfelder, W. J. Johnson, W. S. Gibbons, J. F. 'Impurity Distribution Profiles in Ion-Implanted Silicon' <i>Can. J. Phys.</i> , 46, 597-606 (1968) <i>Comment</i> : R, dR. 10-70 keV B, N, P, As -> Si (Cryst.)	1968-Klei
<b>1968</b>	Manchester, K. E. 'Radiotracer Study of Ion Implanted Profile Build-Up in Silicon Substrates' <i>J. Electrochem. Soc.</i> , 115, 656-59 (1968) <i>Comment</i> : R, dR. 40 keV 31P, 32P -> Si (Cryst.)	1968-Manc
<b>1968</b>	Roosild, S. Dolan, R. Buchanan, B. 'Semiconductor Doping by High Energy 1 - 2.5 MeV Ion Implantation.' <i>J. Electrochem. Soc.</i> , 115, 307-11 (1968) <i>Comment</i> : R, dR. 1-2.5 MeV B, 1-1.6 MeV N, 1 MeV P -> Si. Electrical Junction Measurements.	1968-Roos
<b>1968</b>	Volod'ko, V. G. Zorin, E. I. Pavlov, P. V. Tetel'Baum, D. I. 'Distribution and Range of Boron and Phosphorus Ions used in Bombardment of SiO2' <i>Fiz. Tverd. Tela</i> , 10, 1048-52 (1968) [ <i>Engl. Trans. Sov. Phys. Solid State</i> , 10, 828-31 (1968)] <i>Comment</i> : R, dR. 30-100 keV B, 50-150 keV P -> SiO2	1968-Volo
<b>1969</b>	Andersen, T. Sorensen, G. 'A Sectioning Technique for Copper, Silver, and Gold and Its Application to Penetration and Diffusion Studies' <i>Rad. Effects</i> , 2, 111-17 (1969) <i>Comment</i> : R, dR. (30-400) keV Cu, Co, P, Kr -> Cu, Ag, Au	1969-Ande3
<b>1969</b>	Davies, D. E. 'Range of Implanted Boron, Phosphorus, and Arsenic in Silicon' <i>Can. J. Phys.</i> , 47, 1750-53 (1969) <i>Comment</i> : R, dR. 0.15-1.8 MeV B, 1.0-1.7 MeV As, 0.5-1.7 MeV P -> Si	1969-Davi

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1969	Fairfield, J. M. Crowder, B. L. 'Ion Implantation Doping of Silicon for Shallow Junctions' <i>Trans. Met. Soc. Aime, 245, 469-473 (1969)</i> <i>Comment : R,dR. 70-280 keV B, P, 80-480 keV As -&gt; Si</i>	1969-Fair
1969	Macdonald, J. R. Sidenius, G. 'The Total Ionization in Methane of Ions with $1 \leq Z1 \leq 20$ at Energies from 10 to 120 keV' <i>Phys. Letters A, 28, 543-44 (1969)</i> <i>Comment : S. 10-120 keV H, He, Li, Be, B, C, N, O, F, Ne, Na, Mg, Al, Si, P, S, Cl, Ar, Ca, V, Sc, Ti -&gt; CH4</i>	1969-Macd
1969	Narayanan, G. H. Spitzer, W. G. 'The Structural Characteristics of Radiation Damage Produced by High Energy (2.7 MeV) Ion Implantation in GaAs' <i>J. Matl. Sci., 13, 2418-2428 (1978)</i> <i>Comment : R, dR. N, P (2.7 MeV) -&gt; GaAs</i>	1969-Nara
1970	Bader, R. Kalbitzer, S. 'Low Energy Boron and Phosphorus Implants in Silicon. (B). Doping Profiles.' <i>Rad. Effects, 6, 211-16 (1970)</i> <i>Comment : R, dR. 6 keV B, 15 keV P -&gt; Si (Cryst.).</i>	1970-Bade
1970	Crowder, B. L. 'The Role of Damage in the Annealing Characteristics of Ion Implanted Si' <i>J. Electrochem. Soc., 117, 671-74 (1970)</i> <i>Comment : R, dR. 280 keV 31P -&gt; Si</i>	1970-Crow
1970	Davies, D. E. 'The Implanted Profiles of Boron, Phosphorus, and Arsenic in Silicon from Junction Depth Measurements' <i>Solid-State Elec., 13, 229-237 (1970)</i> <i>Comment : R. 0.1-2.0 MeV B, P, As -&gt; Si</i>	1970-Davi
1970	Dearnaley, G. Wilkens, M. A. Goode, P. D. Freeman, J. H. Gard, G. A. 'The Range Distribution of Radioactive Ions Implanted into Silicon Crystals' <i>W. Palmer, M. W. Thompson, P. D. Townsend: Atomic Collision Phenomena in Solids. North-Holland, Amsterdam, P. 623-55 (1970)</i> <i>Comment : R, dR. 40-120 keV P, Na, S, Cu, Kr -&gt; Si, Cryst. and Amorph.</i>	1970-Dea2
1970	Santry, D. C. Sitter, C. W. 'Range and Retention Studies of 40-keV Ions in Solids, in H' <i>Wagner, W. Walcher (Ed.) Proc. Int. Conf. Elmag. Isotope Separators and Their Techniques. Marburg, P. 505-24 (1970)</i> <i>Comment : R, dR. 40 keV C, O, P, Co, Tl, Na, P, Co, Zn, Se, Kr, Hf, Cs, Ag, I, Xe -&gt; Au, W, WO3</i>	1970-Sant

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1970	Stumpfi, W. Kalbitzer, S. 'Low Energy Boron and Phosphorus Implants in Silicon (a) Electrical Sheet Measurements' <i>Rad. Effects, 6, 205-210 (1970)</i> Comment : R,dR. B, P (7 keV) -> Si	1970-Stum
1970	Wilkins, M. A. Dearnaley, G. 'The Distribution of P32 Channelled into Indium Antimomide' <i>Proc. of the European Conference on Ion Implantation. Peter Peregrinus, Publisher, Stevenhage, England, P. 193-97 (1970)</i> Comment : R, dR. 40 keV 32P -> InSb (Cryst., Axial and Rand.)	1970-Wilk
1971	Crowder, B. L. 'The Influence of the Amorphous Phase on Ion Distributions and Annealing Behavior of Group Iii and Group V Ions Implanted into Silicon' <i>J. Electrochem. Soc., 118, 943-52 (1971)</i> Comment : R,dR. (50-300 keV) B, Al Ga, P, As, Sb, Bi -> Si	1971-Crow
1971	Dearnaley, M. A. Wilkins, M. A. Goode, P. D. 'Non-Gaussian Implantation Profiles' <i>Intl. Conf. Ion Implantation in Semiconductors, Ed. by I. Ruge and J. Graul, 439-454 (1971)</i> Comment : R. 40-120 keV S, P ->Si	1971-Dear
1971	Gusev, V. M. Busharov, N. P. Demakov, K. D. Kozlow, Yu. G. 'Effects of Channeling on the Distribution of Electrically Active Boron and Phosphorus Atoms in Silicon Single Crystals' <i>Dokl. Akad. Nauk. Sssr, 19, 319-22 (1971). [Engl. Trans. Sov. Phys. Doklady, 19, 213-15 (1971).</i> Comment : R, dR. 100 keV B, 150 keV P -> Si (Cryst. And Random)	1971-Guse
1971	Hogberg, G. 'Electronic and Nuclear Stopping Cross Sections in Carbon' <i>Phys. Stat. Sol. B, 48, 829-41 (1971)</i> Comment : S. (10-46 keV) Li, B, N, C, O, F, Ne, Na, P, Ar -> C	1971-Hogb
1971	Moline, R. A. Reutlinger, G. W. 'Phosphorus Channeled in Silicon: Profiles and Electrical Activity' <i>In I. Ruge and J. Graul: Ion Implantation in Semiconductors. Springer, Berlin. p. 58-69 (1971)</i> Comment : R,dR. 100-300 keV P -> Si (Cryst.)	1971-Moli2
1971	Ziegler, J. F. Crowder, B. L. Kleinfelder, W. J. 'Experimental Evaluation of High Energy Ion Implantation Gradients for Possible Fabrication of a Transistor Pedastal Collector' <i>IBM J. Res. and Dev., 15, 452-456 (1971)</i> Comment : R, dR. 2-4 MeV B, P -> Si	1971-Zieg

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1972	Hogberg, G. Skoog, R. 'Non-Evidence for Z1, Oscillations of the Nuclear Ion-Atom Interaction in an Amorphous Target' <i>Rad. Effects, 13, 197-202 (1972)</i> <i>Comment : S. 50 keV Li, B, C, N, O, F, Ne, Na, Mg, P, Ar -&gt; C</i>	1972-Hogb
1972	Krylow, J. Rosinski, W. Saczuk, K. 'Study of the Concentration Profiles of Phosphorus and Boron Implanted into Silicon' <i>Electron Tech., 5, 109-117 (1972)</i> <i>Comment : R. 30 keV P, 40 keV B -&gt; Si</i>	1972-Kryl
1972	Morabito, J. M. Tsai, J. C. 'In-Depth Profiles of Phosphorus Ion-Implanted Silicon by Auger Spectroscopy and Secondary Ion Emission' <i>Surf. Sci., 33, 422-426 (1972)</i> <i>Comment : R. 50 keV P -&gt; Si</i>	1972-Mora
1972	Pavlov, P. V. Zorin, E. I. Tetel'Baum, D. I. Baranova, A. S. Vasil'Ev, V. K. 'On the Influence of Channeling and Anomalous Diffusion on the Profiles of Implanted Phosphorus and Boron Atoms Silicon' <i>Rad. Effects, 13, 153-155 (1972)</i> <i>Comment : R. 40-100 keV P, B -&gt; Si</i>	1972-Pavl
1972	Reddi, V. G. Sanbury, J. D. 'Channeling of Phosphorus Ions in Silicon' <i>Appl. Phys. Letters, 20, 30-31 (1972)</i> <i>Comment : R,dR. 30-600 keV 31P -&gt; Si (Cyrst.)</i>	1972-Redd
1973	Blood, P. Dearnaley, G. Wilkens, M. A. 'The Depth Distribution of Phosphorus Ions Implanted into Silicon Crystals' <i>B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 75-85 (1973)</i> <i>Comment : R,dR. 40-120 keV 32P -&gt; Si (Cryst. And Amorph.)</i>	1973-Bloo
1973	Golanski, A. Dybczynski, R. 'Implantation of Ions. II. Study on the Distributions of Effective Ranges of Phosphorus Atoms Implanted into Silicon Monocrystal (In Polish).' <i>Nukleonika, 18, 351-66 (1973)</i> <i>Comment : R, dR. 16-60 keV P -&gt; Si</i>	1973-Gola
1973	Kostka, A. Kalbitzer, S. 'Integrated dE-E Detector System made by Ion Implantation' <i>Appl. Phys. Letters, 23, 704-706 (1973)</i> <i>Comment : R. B (8 MeV), P (6 keV) -&gt; Si</i>	1973-Kost
1973	Okabayashi, H. Shinoda, D. 'Lateral Spread of 31P and 11B Ions Implanted in Silicon' <i>J. Appl. Phys., 44, 4220-21 (1973)</i> <i>Comment : R, dR, dR(Lateral). 145, 260 keV 31P; 80, 150 keV 11B -&gt; Si</i>	1973-Okab

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<b>1973</b>	Reddi, V. G. K. Sansbury, J. D. 'Channeling and Dechanneling of Ion-Implanted Phosphorus in Silicon' <i>J. Appl. Phys.</i> , 44, 2951-63 (1973) <i>Comment</i> : R,dR. 30-900 keV 31P -> Si (Cryst.)	1973-Redd
<b>1974</b>	Blood, P. Dearnaley, G. Wilkins, M. A. 'The Origin of Non-Gaussian Profiles in Phosphorus-Implanted Silicon' <i>J. Appl. Phys.</i> , 45, 5123-5128 (1974) <i>Comment</i> : R, dR. P -> Si ([110], [100])	1974-Bloo
<b>1974</b>	Blood, P. Dearnaley, G. Wilkens, M. 'The Depth Distribution of Phosphorus Ions Implanted into Silicon Crystals' <i>Rad. Effects</i> , 21, 245-51 (1974) <i>Comment</i> : R, dR. 40-120 keV 32P -> Si (Cryst. And Amorph.)	1974-Bloo2
<b>1974</b>	Burkhardt, F. Mertens, A. Wagner, C. 'Concentration Profiles of Implanted Phosphorus in Silicon' <i>Phys. Stat. Sol. A</i> , 22, K45-47 (1974) <i>Comment</i> : R. 50 keV P -> Si	1974-Burk
<b>1974</b>	Cembali, F. Galloni, R. Mousty, F. Rosa, R. Zignani, F. 'Doping and Radiation Damage Profiles in Silicon Along the [110] Axis' <i>Rad. Effects</i> , 21, 255-64 (1974) <i>Comment</i> : R, dR. 200 keV P -> Si (Cryst.)	1974-Cemb
<b>1974</b>	Jensen, M. Larsson, L. Mathiesen, O. Rosander, R. 'Experimental and Theoretical Absorptance Profiles of Tracks of Fast Heavy Ions in Nuclear Emulsion' <i>Univ. Lund., Sweden</i> (1974) <i>Comment</i> : R. 0.3 < Beta < 0.8 Si, P, Ca, Cr, Fe -> Emulsion	1974-Jens
<b>1974</b>	Okabayashi, H. Daizaburo, S. 'Range and Standard Deviation of Ion-Implanted Phosphorus and Boron in Silicon' <i>NEC Res. and Dev.</i> , 35, 10-14 (1974) <i>Comment</i> : R, dR. 50-260 keV P, B -> Si	1974-Okab
<b>1974</b>	Okabayashi, H. Shinoda, D. 'Range and Standard Deviation of Ion-Implanted Phosphorus in Silicon' <i>Jap. J. Appl. Phys.</i> , 13, 1187-88 (1974) <i>Comment</i> : R. 50-145 keV 31P -> Si	1974-Okab2
<b>1974</b>	Pan, E. Fang, F. F. 'Lateral Spread of Ion Implanted Impurities in Silicon' <i>J. Appl. Phys.</i> , 45, 2801-2803 (1974) <i>Comment</i> : R. B, P (20-70 keV) -> Si One of the earliest lateral-spread range measurements.	1974-Pan

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<b>1975</b>	Gashtol'D, V. N. Gerasimenko, N. N. Dvurechenskii, A. V. Smirnov, L. S. 'Profiles of Defects Produced by the Implantation of Ions in Silicon' <i>Sov. Phys. Semicond.</i> , <b>9</b> , 551-553 (1975) <i>Comment</i> : R. Profiles Of Defects (40-250 keV) Ar, B, P -> Si	1975-Gash
<b>1976</b>	Kachare, A. H. Spitzer, W. G. Fredrickson, J. E. Euler, F. K. 'Measurements of Layer Thicknesses and Refractive Indices in High Energy Ion Implanted GaAs and GaP' <i>J. Appl. Phys.</i> , <b>47</b> , 5347-5381 (1976) <i>Comment</i> : R. N, P (3 MeV) -> GaAs, GaP	1976-Kach
<b>1976</b>	Natsuaki, N. Tamura, M. Tokuyama, T. 'Low Energy and High Dose Phosphorus Ion Implantation into Silicon through SiO <sub>2</sub> Film' <i>Jap. J. Appl. Phys.</i> , <b>15</b> , 2427-2432 (1976) <i>Comment</i> : R. 3 keV P -> Si, SiO <sub>2</sub>	1976-Nats
<b>1977</b>	Bogh, E. Hogild, P. Stensgaard, I. 'Spatial Distribution of Defects in Ion Bombarded Silicon and Germanium' <i>Rad. Effects</i> , <b>7</b> , 115-121 (1977) <i>Comment</i> : R. 10-400 keV P, Sb -> Si, Ge	1977-Bogh
<b>1977</b>	Das, G. 'Analysis of Defects in P-Implanted Silicon' <i>Electrochem. Soc. Extended Abstracts</i> , <b>190</b> , May (1977) <i>Comment</i> : R. 50 keV P -> Si	1977-Das
<b>1977</b>	Hirao, T. Inoue, K. Takayanagi, S. Yaegashi, Y. 'Depth Distribution of Knock-On Nitrogen in Si by Phosphorus Implantation through Si <sub>3</sub> N <sub>4</sub> Films' <i>Appl. Phys. Letters</i> , <b>31</b> , 505-508 (1977) <i>Comment</i> : R. 100-220 keV P, N -> Si	1977-Hira
<b>1978</b>	Alexander, T. K. Forster, J. S. Ball, G. C. Davies, W. G. Winterbon, K. B. 'Z <sub>1</sub> and Z <sub>2</sub> Variations in the Stopping Powers of Z <sub>1</sub> =10-18 Ions Deduced from DSAM Lifetime Measurements' <i>Phys. Letters</i> , <b>74B</b> , 183-186 (1978) <i>Comment</i> : S. Ne, Na, Mg, Al, Si, P, S, Ar (3-4 MeV) -> Cu, Ni, Ta, Au, Mg, Ca, Ti, Ba. Doppler shift lifetime measurements.	1978-Alex
<b>1978</b>	Battaglin, G. DellaMea, G. Drigo, A. V. Foti, G. Bentini, G. G. 'Two-Stage Laser Annealing of Lattice Disorder in Phosphorus Implanted Silicon' <i>Phys. Stat. Sol. A</i> , <b>49</b> , 347-352 (1978) <i>Comment</i> : R, dR. 100 keV 31P -> Si	1978-Batt
<b>1978</b>	Furuya, T. Nishi, H. Inada, T. Sakurai, T. 'Channeled-Ion Implantation of Group-III and Group-V Ions into Silicon' <i>J. Appl. Phys.</i> , <b>49</b> , 3918-3921 (1978). <i>Comment</i> : R, dR. 100-300 keV B, P, As, Al, Ga -> Si [111], [110], Random	1978-Furu

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1978	Miyao, M. Tamura, M. Tokuyama, T. 'Selective Annealing of Ion-Implanted Amorphous Layers by Nd <sup>3+</sup> -Yag Laser Irradiation' <i>Appl. Phys. Letters</i> , 33, 828-830 (1978) Comment : R, dR. 50 keV P -> Si	1978-Miya
1978	Miyao, M. Yoshihiro, N. Tokuyama, T. Mitsuishi, T. 'Correlation Between Lattice Damage and Electrical Activation of Phosphorus-Implanted Silicon' <i>J. Appl. Phys.</i> , 49, 2573-2575 (1978) Comment : R. 50 keV P -> Si	1978-Miya2
1978	North, J. C. Adams, A. C. Richards, G. F. 'Ion Implantation Doping of Polycrystalline Silicon' <i>Extend. Abs. Electrochem.</i> , 78, 540 (1978) Comment : R. 150 keV B, As; 300 keV P -> Si	1978-Nort
1978	Picraux, S. T. Follstaedt, D. M. Baeri, P. Campisano, S. U. Foti, G. 'Depth Profile Studies of Extended Defects Induced by Ion Implantation in Si and Al' <i>Proc. Intl. Conf. Ion Beam Modification of Materials</i> (1978) Comment : R, dR. 200 keV P -> Si; 150 keV Ni -> Al	1978-Picr
1978	White, C. W. Christie, W. H. Appleton, B. R. Wilson, S. R. Pronko, P. P. 'Redistribution of Dopants in Ion-Implanted Silicon by Pulsed-Laser Annealing' <i>Appl. Phys. Letters</i> , 33, 662-664 (1978) Comment : R, dR. 35 keV 11B, 80 keV 31P, 100 keV 75As -> Si	1978-Whit
1979	Andrews, H. R. Lennard, W. N. Mitchell, I. V. Ward, D. Phillips, D. 'Low Energy Stopping Powers Determined by Time of Flight Techniques' <i>IEEE Trans. Nucl. Sci.</i> , NS-26, 1326-1330 (1979) Comment : S. (0.180 <vel.< 0.219 cm/ns) (6 <= Z1 <= 20)-> C, Al, Ni, Ag, Au	1979-Andr
1979	Greenwald, A. C. Kirkpatrick, A. R. Little, R. G. Minnucci, J. A. 'Pulsed-Electron-Beam Annealing of Ion-Implantation Damage' <i>J. Appl. Phys.</i> , 50, 783-787 (1979) Comment : R, dR. 10 keV P -> Si [111]	1979-Gree
1979	Hirao, T. Inoue, K. Takayanagi, S. Yaegashi, Y. 'The Concentration Profiles of Projectiles and Recoiled Nitrogen in Si after Ion Implantation through Si <sub>3</sub> N <sub>4</sub> Films' <i>J. Appl. Phys.</i> , 50, 193-201 (1979) Comment : R, dR. 160 keV P -> Si, 355 keV As -> Si, 50 keV B -> Si, 200 keV Ar -> Si	1979-Hira2
1979	Hirao, T. Inoue, K. Yaegashi, Y. Takayanagi, S. 'The Concentration Profiles of Phosphorus, Arsenic and Recoiled Oxygen Atoms in Si by Ion Implantation into SiO <sub>2</sub> -Si' <i>Jap. J. Appl. Phys.</i> , 18, 647-656 (1979) Comment : R, dR. 70-350 keV P, 180 keV As -> Si Through SiO <sub>2</sub>	1979-Hira3



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1979	Hubler, G. K. Waddell, C. N. Spitzer, W. G. Fredrickson, J. E. Prussin, S. 'High-Fluence Implantations of Silicon: Layer Thickness and Refractive Indices' <i>J. Appl. Phys.</i> , 50, 3294-3303 (1979) <i>Comment</i> : R, dR. 0.20-2.7 MeV P, 0.30 MeV Si -> Si	1979-Hubl2
1979	Inoue, K. Hirao, T. Yaegashi, Y. Takayanagi, S. 'Asymmetrical Profiles of Ion Implanted Phosphorus in Silicon' <i>Jap. J. Appl. Phys.</i> , 18, 367-372 (1979) <i>Comment</i> : R, dR. 150-300 keV P -> Si	1979-Inou
1979	Krynicky, J. Bourgoin, J. C. 'Defect Annealing in Phosphorus Implanted Silicon: A D.L.T.S. Experiment on Phosphorus Implants.' <i>Appl. Phys.</i> , 18, 275-278 (1979) <i>Comment</i> : R, dR. 130 keV P -> Si	1979-Kryn
1979	Magee, C. W. 'Depth Profiling of N-Type Dopants in Si and GaAs using Cs+ Bombardment Negative Secondary Ion Mass Spectrometry in Ultrahigh Vacuum' <i>J. Electrochem. Soc.</i> , 126, 660-663 (1979) <i>Comment</i> : R, dR. 15 keV H, 80 keV P, 200 keV As -> Si; 200 keV Si, 250 keV S -> GaAs	1979-Mage
1979	Miyao, M. Yoshihiro, N. Tokuyama, T. Mitsuishi, T. 'Damage-Dependent Electrical Activation of Ion-Implanted Silicon. I. Experiments on Phosphorus Implants.' <i>J. Appl. Phys.</i> , 50, 223-230 (1979) <i>Comment</i> : R, dR. 50 keV P -> Si	1979-Miya
1979	Pham, M. T. 'A Very Simple Method for Profiling the Ion-Implanted Si-Surface' <i>Phys. Stat. Sol. A</i> , 49, 261-265 (1979) <i>Comment</i> : R. 30 keV Si, P, B, Ar, As; 12.2 keV In -> Si	1979-Pham
1979	Sakurai, T. Kawata, H. Sato, T. Hisatsugu, T. Hashimoto, H. 'Lateral Spread of P+ Ions Implanted in Silicon through the SiO2 Mask Window' <i>J. Appl. Phys.</i> , 50, 1287-1290 (1979) <i>Comment</i> : R, dR. 150 keV P -> Si	1979-Saku
1979	Santry, D. C. Werner, R. D. Westcott, O. M. 'The Range of 120 keV Ions in Solids' <i>IEEE Trans. Nucl. Sci.</i> , Ns-26, 1331-1334 (1979) <i>Comment</i> : R, dR. 120 keV Mg, Al, P, S, Cl, K, Ar, Cr, Mn, Cu, Zn, Ga, As, Br, Kr, Rb, Ag, In, Sn, Sb, Te, I, Xe, Cs, Ba, Pr, Au, Hg, Tl, Pb, Bi -> Be, C, Al, Si	1979-Sant
1979	Ward, D. Andrews, H. R. Mitchell, I. V. Lennard, W. N. Walker, R. B. 'Systematics for the Z1-Oscillation in Stopping Powers of Various Solid Materials' <i>Can. J. Phys.</i> , 57, 645-656 (1979). <i>Comment</i> : S. (vel.=0.18-0.22 cm/ns) C, N, O, F, Ne, Na, Mg, Al, Si, P, S, Cl, Ar, K, Ca -> C, Al, Ni, Ag, Au	1979-Ward

# Citations for Ion : **P**

<b>Pub. Year</b>	<b>Authors, Title, Journal Citation and Comments</b>	<b>Citation Numb</b>
<b>1979</b>	White, C. W. Christie, W. H. Pronko, P. P. Appleton, B. R. Wilson, S. R. 'Dopant Profile Changes Induced by Pulsed Laser Annealing' <i>Rad. Effects, 47, 37-40 (1979)</i> <i>Comment : R, dR. 35-150 keV B, P, As, Sb, Cu, Fe -&gt; Si</i>	<b>1979-Whit</b>
<b>1980</b>	Desalvo, A. Galloni, R. Rosa, R. Zignani, F. 'Experimental and Computer Analysis of P+-Ion Penetration Tails in a SiO <sub>2</sub> -Si Two Layer System' <i>J. Appl. Phys., 51, 1994-1997 (1980)</i> <i>Comment : R, dR. 150-keV P -&gt; Si</i>	<b>1980-Desa</b>
<b>1980</b>	Hirao, T. Inoue, K. Fuse, G. Takayanagi, S. T. Yaegashi, Y. 'The Concentration Profiles of the Recoil Implanted Oxygen in Si after Ion Implantations into SiO <sub>2</sub> -Si Substrates' <i>Rad. Effects, 47, 95-98 (1980)</i> <i>Comment : R, dR. 100-220 keV P, Ar, As -&gt; Si</i>	<b>1980-Hira2</b>
<b>1980</b>	Josquin, W. J. M. J. 'The Oxidation Characteristics of Nitrogen-Implanted Silicon' <i>Rad. Effects, 47, 221-224, (1980)</i> <i>Comment : R, dR. 250-800 keV H, H<sub>2</sub>, He, B, P -&gt; Si</i>	<b>1980-Josq</b>
<b>1980</b>	Kalbitzer, S. Oetzmann, H. 'Ranges and Range Theories' <i>Rad. Effects, 47, 57-72, (1980)</i> <i>Comment : R, dR. .1-2 MeV Bi, Sb, As, Ge, P, Au, Cs, Eu, Gd Tb -&gt; Si, Ge, C, Al</i>	<b>1980-Kalb</b>
<b>1980</b>	Sofield, C. J. Cowern, N. E. B. Freeman, J. M. 'Charge-Exchange Effects in Energy-Loss Straggling' <i>Nucl. Inst. Methods, 170, 221-225 (1980)</i> <i>Comment : R, dR. 0-50 MeV Atomic Numbers 1-16 -&gt; Al</i>	<b>1980-Sofi</b>
<b>1980</b>	Tashlykov, I. S. 'Backscattering Measurements of P+ Implanted GaAs Crystals' <i>Nucl. Inst. Methods, 170, 403-406 (1980)</i> <i>Comment : R, dR. 30-60 keV P -&gt; GaAs</i>	<b>1980-Tash</b>
<b>1985</b>	Ingrahm, D. C. Baker, J. A. Walsh, D. A. 'Range Distributions of MeV Implants in Silicon' <i>Nucl. Inst. Methods, B7/8, 361-365 (1985)</i> <i>Comment : R, dR. B, P, Sb (0.4-6 MeV) -&gt; Si</i>	<b>1985-Ingr</b>
<b>1986</b>	Lennard, W. N. Geissel, H. Phillips, D. Jackson, D. P. 'Heavy Ion Straggling: Possible Evidence for Inner-Shell Excitation' <i>Phys. Rev. Letters, 57, 318-320 (1986)</i> <i>Comment : dS.F, Ne, Na, Mg, Al, Si, P, S, Cl, Ar, K, Sc (16 keV/amu) -&gt; C</i>	<b>1986-Lenn</b>

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1986	Lennard, W. N. Geissel, H. Jackson, D. P. Phillips, D. 'Electronic Stopping Values for Low Velocity Ions ( $9 \leq Z_1 \leq 92$ ) in Carbon Targets' <i>Nucl. Inst. Methods, B13, 127 (1986)</i> <i>Comment</i> : S. (16 keV/amu) F, Ne, Na, Mg, Al, P, Cl, Ar, K, Sc, Cr, Mn, Cu, Kr, Nb, Ag, In, Xe, Sm, Yb, Au, Bi, U -> C	1986-Lenn2
1986	Wilson, R. G. 'Random and Channeled Implantation Profiles and Range Parameters for P and Al in Crystalline and Amorphized Si' <i>J. Appl. Phys., 60 (8), 2797-2805 (1986)</i> <i>Comment</i> : R, dR. P, Al (25-600 keV) -> Si	1986-Wils
1987	Ingram, D. C. Baker, J. A. Walsh, D. A. Strathman, E. 'Range Distributions of MeV Implants in Silicon - 2' <i>Nucl. Inst. Methods, B21, 460-465 (1987)</i> <i>Comment</i> : R, dR. B, P, Ga (0.4-6.0 MeV) -> Si	1987-Ingr
1987	Skorupa, W. Wieser, E. Groetzschel, R. Posselt, M. Buecke, H. 'High Energy Implantation and Annealing of Phosphorus in Silicon' <i>Nucl. Inst. Methods, B19/20, 335-339 (1987)</i> <i>Comment</i> : R. P (1 MeV) -> Si	1987-Skor
1988	Wilson, R. G. '(111) Random and (110) Channeling Implantation Profiles and Range Parameters in HgCdTe' <i>J. Appl. Phys., 63, 5302-5311 (1988)</i> <i>Comment</i> : R, dR. 45 Ions (H to Ta) at 100-700 keV -> HgCdTe	1988-Wils
1988	Wilson, R. G. 'Ion Implantation and SIMS Profiling of Impurities in II-VI Materials HgCdTe and CdTe' <i>J. Crystal Growth, 86, 735-743 (1988)</i> <i>Comment</i> : R, dR. 52 Ions (H-Hg) at 100-700 keV -> CdTe, HgCdTe	1988-Wils2
1989	Tikkanen, P. 'Electronic Stopping Power of Ta for $Z=11-18$ Atoms at Energies 0-0.8 MeV/amu' <i>Nucl. Inst. Methods, B36, 103 (1989)</i> <i>Comment</i> : S. Na, Mg, Al, Si, P, S, Cl, Ar (0-0.8 MeV/amu) -> Ta	1989-Tikk
1990	Blank, B. Gaimard, J. J. Geissel, H. Munzenberg, G. Schmidt, K. H. 'Energy Loss Measurements with Heavy Ions at Relativistic Energies' <i>Nucl. Inst. Methods, B51, 85-88 (1990)</i> <i>Comment</i> : S. Ar, P, N, Li (130-401 MeV/amu) -> C, Al, Pb	1990-Blan
1990	Raisanen, J. Rauhala, E. 'Stopping Powers and Energy Loss of Mylar, Kapton, Havar and Ni for 10 Ions ( $Z=3-17$ ) in the Energy Range 0.2-2.1 MeV/amu' <i>Phys. Rev. B, 41, 3951-3958 (1990)</i> <i>Comment</i> : S. B, C, N, O, Al, Si, P, Cl (0.2-2.1 MeV/amu) -> Mylar, Kapton, Havar, Ni	1990-Rais

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1991	Kuronen, A. 'A Study of Stopping Power using Nuclear Methods' <i>Comm. Physico-Math. (Finland), 122, 1-36 (1991)</i> <i>Comment : S. Ion [Z=3-22] at (0-0.4 Vo) -&gt; Solids (Z=14-82)</i>	1991-Kuro
1992	Keinonen, J. Arstila, K. Tikkanen, P. 'Electronic Stopping Power of Si and Ge for MeV Energy Si Ions' <i>Appl. Phys. Letters, 60, 228-230 (1992)</i> <i>Comment : S. Si, P (0-30 MeV) -&gt; Si, Ge</i>	1992-Kein
1995	Randhawa, G. S. Garg, A. K. Virk, H. S. 'Range Study of Heavy Ions in Plastic Track Detectors' <i>Rad. Meas. (UK), 24, 197-199 (1995)</i> <i>Comment : R. Heavy Ions (10-17 MeV/amu) -&gt; Lexan</i>	1995-Rand
1996	Gelfort, S. Kerkow, H. Stolle, R. Petukhov, V. P. Romanowski, E. A. 'Angular Dependence of the Electronic Energy Loss for Low Energy Heavy Ions under Channeling Conditions' <i>Nucl. Inst. Methods, B115, 315-318 (1996)</i> <i>Comment : S. Channeling of ions He to Kr in Si &lt;110&gt;</i>	1996-Gelf
1996	Hari, K. V. Pathak, A. P. Sharma, S. K. Shyam, K. Nath, N. 'Energy Loss of MeV Heavy Ions in Carbon' <i>Nucl. Inst. Methods, B108, 223-226 (1996)</i> <i>Comment : S. Z1 (O - Cu) at 0.1-1.0 MeV/amu -&gt; C</i>	1996-Hari
1999	Jiang, W. Grotzschel, W. Pilz, W. Schmidt, B Moller, W. 'Random and Channeling Stopping Powers and Charge State Distributions in Silicon for 0.2 - 1.2 MeV/u Positive Heavy Ions' <i>Phys. Rev. B, 59, 226-234 (1999)</i> <i>Comment : S. Li, B, C, N, O, P, Cl (0.2 - 1.2 MeV/u) -&gt; Si</i>	1999-Jian
2002	Whitlow, H. J. Timmers, H. Elliman, R. G. Weijers, T. D. Zhang, Y. 'Measurement and Uncertainties of Energy Loss in Silicon over a Wide Z1 Range using Time-of-Flight Detector Telescopes' <i>Nucl. Inst. Methods, B195, 133-146 (2002)</i> <i>Comment : S. Li, Be, B, C, N, O, F, Na, Mg, Al, Si, P, Mn, Fe -&gt; Si</i>	2002-Whit2
2004	Janson, M.S. Linnarsson, M.K. Hallen, A Svensson, B.G. 'Electronic stopping cross sections in silicon carbide for low-velocity ions with $1 \leq Z1 \leq 15$ ' <i>J. Appl. Phys. 96, 164 (2004)</i> <i>Comment : S. H - P (1.5-300 keV) -&gt; SiC</i>	2004-Jans
2004	Nigam, M. Duggan, J.L. Bounanani, M. El. Yang, C. Ravi, G. V. 'Stopping power of thin GaAs films for Si and P ions' <i>Nucl. Instrum. Methods B219-220, 273 (2004)</i> <i>Comment : S. Si, P (0.07 - 0.3 MeV/n) -&gt; GaAs</i>	2004-Niga

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<i>Pub. Year</i>	<i>Authors, Title, Journal Citation and Comments</i>	<i>Citation Numb</i>
<b>2007</b>	Yu, Y.C. Hsu, J.Y. Chen, K.M. 'Energy loss in polycarbonate and polyethylene terephthalate by 2.0-6.5 MeV <sup>14</sup> N, <sup>31</sup> P and <sup>75</sup> As ions' <i>Nucl. Instrum. Methods B 261 (2007) 1184 (2007)</i> <i>Comment : S. N (2-6 MeV), P (3.0-6.5 MeV), As (3.0-6.5 MeV) -&gt; polycarbonate, polyethylene terephthalate</i>	2007-Yu

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